



STGB20NB32LZ STGB20NB32LZ-1

N-CHANNEL CLAMPED 20A - D²PAK/I²PAK INTERNALLY CLAMPED PowerMESH™ IGBT

TYPE	V _{CES}	V _{CE(sat)}	I _c
STGB20NB32LZ	CLAMPED	< 2.0 V	20 A
STGB20NB32LZ-1	CLAMPED	< 2.0 V	20 A

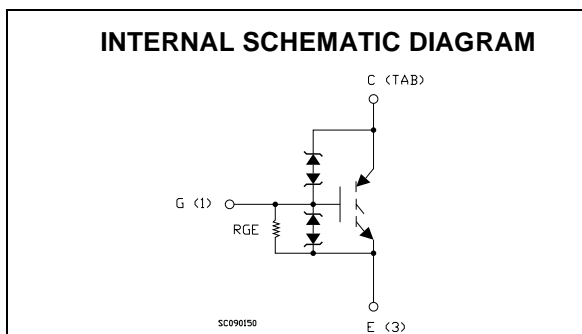
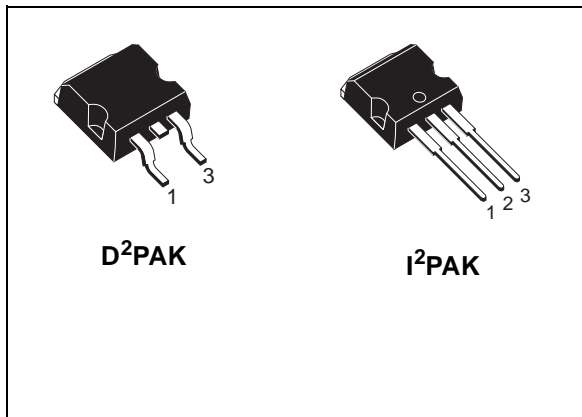
- POLYSILICON GATE VOLTAGE DRIVEN
- LOW THRESHOLD VOLTAGE
- LOW ON-VOLTAGE DROP
- HIGH CURRENT CAPABILITY
- HIGH VOLTAGE CLAMPING FEATURE

DESCRIPTION

Using the latest high voltage technology based on a patented strip layout, STMicroelectronics has designed an advanced family of IGBTs, the PowerMESH™ IGBTs, with outstanding performances. The built in collector-gate zener exhibits a very precise active clamping while the gate-emitter zener supplies an ESD protection.

APPLICATIONS

- ELECTRONIC IGNITION FOR AUTOMOTIVE



ORDERING INFORMATION

SALES TYPE	MARKING	PACKAGE	PACKAGING
STGB20NB32LZT4	GB20NB32LZ	D ² PAK	TAPE & REEL
STGB20NB32LZ-1	GB20NB32LZ	I ² PAK	TUBE

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ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CES}	Collector-Emitter Voltage ($V_{GS} = 0$)	CLAMPED	V
V_{ECR}	Reverse Battery Protection	20	V
V_{GE}	Gate-Emitter Voltage	CLAMPED	V
I_C	Collector Current (continuous) at $T_C = 25^\circ\text{C}$	40	A
I_C	Collector Current (continuous) at $T_C = 100^\circ\text{C}$	30	A
$I_{CM}(\bullet)$	Collector Current (pulsed)	80	A
E_{as}	Single Pulse Energy $T_C = 25^\circ\text{C}$	700	mJ
P_{tot}	Total Dissipation at $T_C = 25^\circ\text{C}$	150	W
	Derating Factor	1	W/°C
E_{SD}	ESD (Human Body Model)	4	KV
T_{stg}	Storage Temperature	-65 to 175	°C
T_j	Max. Operating Junction Temperature	175	°C

(*)Pulse width limited by safe operating area

THERMAL DATA

$R_{thj-case}$	Thermal Resistance Junction-case Max	1	°C/W
$R_{thj-amb}$	Thermal Resistance Junction-ambient Max	62.5	°C/W

ELECTRICAL CHARACTERISTICS ($T_{CASE} = 25^\circ\text{C}$ UNLESS OTHERWISE SPECIFIED)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$BV_{(CES)}$	Clamped Voltage	$I_C = 2\text{ mA}, V_{GE} = 0, T_C = -40^\circ\text{C}$	330	355	380	V
		$I_C = 2\text{ mA}, V_{GE} = 0, T_C = 25^\circ\text{C}$	325	350	375	V
		$I_C = 2\text{ mA}, V_{GE} = 0, T_C = 150^\circ\text{C}$	320	345	370	V
$BV_{(ECR)}$	Emitter Collector Break-down Voltage	$I_C = 75\text{ mA}, T_C = 25^\circ\text{C}$	20	28		V
BV_{GE}	Gate Emitter Break-down Voltage	$I_G = \pm 2\text{ mA}$	12	14	16	V
I_{CES}	Collector cut-off Current ($V_{GE} = 0$)	$V_{CE} = 15\text{ V}, V_{GE} = 0, T_C = 150^\circ\text{C}$			10	μA
		$V_{CE} = 200\text{ V}, V_{GE} = 0, T_C = 150^\circ\text{C}$			100	μA
I_{GES}	Gate-Emitter Leakage Current ($V_{CE} = 0$)	$V_{GE} = \pm 10\text{ V}, V_{CE} = 0$	± 400	± 660	± 1000	μA
R_{GE}	Gate Emitter Resistance		10	15	25	K Ω

ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GE(th)}$	Gate Threshold Voltage	$V_{CE} = V_{GE}, I_C = 250\mu\text{A}, T_C = -40^\circ\text{C}$	1.2			V
		$V_{CE} = V_{GE}, I_C = 250\mu\text{A}, T_C = 25^\circ\text{C}$	1	1.4	2	V
		$V_{CE} = V_{GE}, I_C = 250\mu\text{A}, T_C = 150^\circ\text{C}$	0.6			V
$V_{CE(SAT)}$	Collector-Emitter Saturation Voltage	$V_{GE} = 4.5\text{ V}, I_C = 10\text{ A}, T_C = 25^\circ\text{C}$		1.1	1.8	V
		$V_{GE} = 4.5\text{ V}, I_C = 10\text{ A}, T_C = 150^\circ\text{C}$		1	1.7	V
		$V_{GE} = 4.5\text{ V}, I_C = 20\text{ A}, T_C = 25^\circ\text{C}$		1.35	2	V
		$V_{GE} = 4.5\text{ V}, I_C = 20\text{ A}, T_C = 150^\circ\text{C}$		1.25	2	V

ELECTRICAL CHARACTERISTICS (T_{CASE} = 25 °C UNLESS OTHERWISE SPECIFIED)
DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs}	Forward Transconductance	V _{CE} = 25 V , I _C =20 A		35		S
C _{ies}	Input Capacitance	V _{CE} = 25 V, f = 1 MHz, V _{GE} = 0		2300		pF
C _{oes}	Output Capacitance			165		pF
C _{res}	Reverse Transfer Capacitance			28		pF
Q _g	Gate Charge	V _{CE} = 280 V, I _C = 20 A, V _{GE} = 5 V		51		nC

FUNCTIONAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I _l	Latching Current	R _{GOFF} =127Ω, V _{Clamp} = 250 V, V _{GE} = 5 V, T _C = 125 °C	34			A
U.I.S.	Functional Test Open Secondary Coil	R _{GOFF} =1KΩ ,T _C =125°C, V _G = 5 V, L = 1.6mH	21.6			A

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
t _{d(on)} t _r	Delay Time Rise Time	V _{CC} = 250 V, I _C = 20 A R _G = 1KΩ , V _{GE} = 4.5 V		2.3 0.6		μs μs
(di/dt) _{on}	Turn-on Current Slope	V _{CC} = 250 V, I _C = 20 A R _G =1KΩ, V _{GE} = 4.5 V		550		A/μs
E _{on}	Turn-on Switching Losses	V _{CC} = 250 V, I _C = 20 A, T _c =25°C R _G =1KΩ, V _{GE} = 4.5 V, T _c =150°C		8.8 9.2		mJ mJ

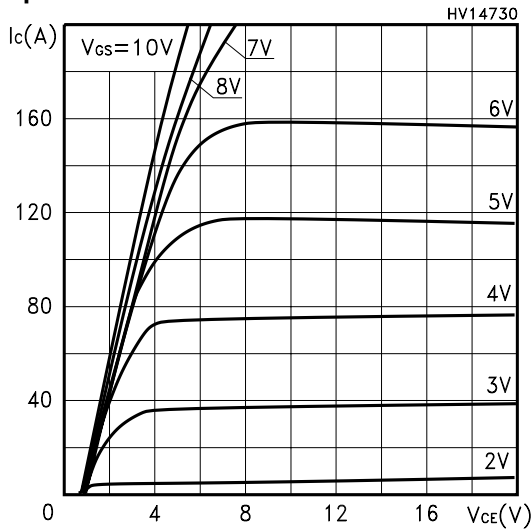
SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
t _c t _r (V _{off}) t _f	Cross-Over Time Off Voltage Rise Time Fall Time	V _{CC} = 250 V, I _C = 20 A, R _{GE} = 1 KΩ , V _{GE} = 4.5 V		4.8 2.6 2		μs μs μs
t _{d(off)}	Off Voltage Delay Time			11.5		μs
E _{off} (**)	Turn-off Switching Loss			11.8		mJ
t _c t _r (V _{off}) t _f t _{d(off)} E _{off} (**)	Cross-Over Time Off Voltage Rise Time Fall Time Off Voltage Delay Time Turn-off Switching Loss	V _{CC} = 250 V, I _C = 20 A, R _{GE} = 1 KΩ , V _{GE} = 4.5 V T _c = 150 °C		7.8 3.5 3.9 12 17.8		μs μs μs μs mJ

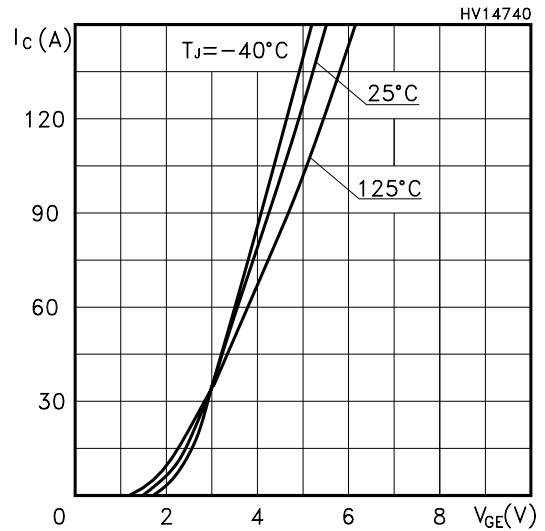
(**)Losses Include Also the Tail (jedec Standardization)

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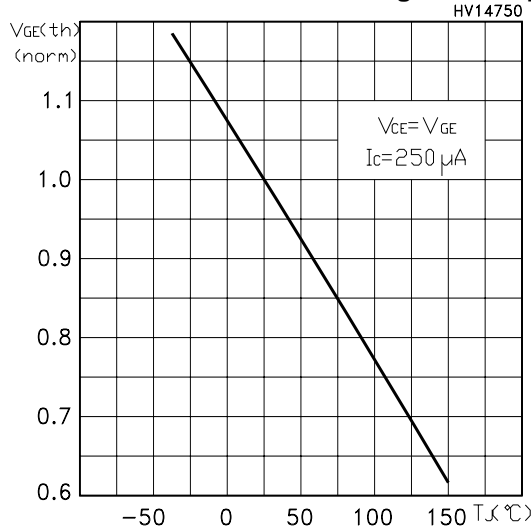
Output Characteristics



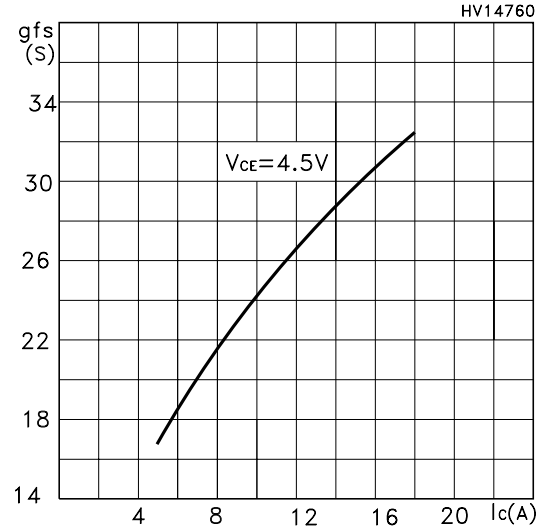
Transfer Characteristics



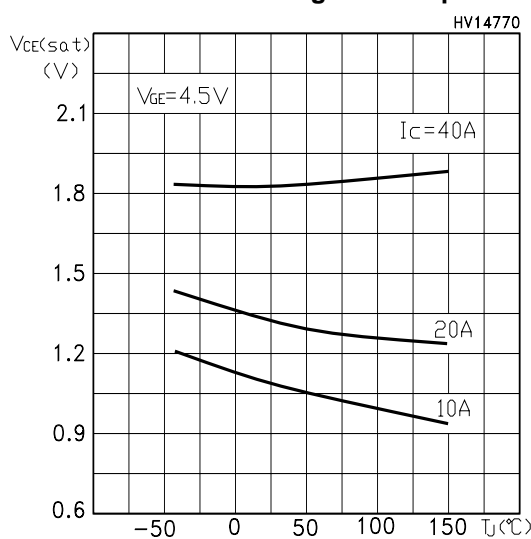
Normalized Gate Threshold Voltage vs Temp.



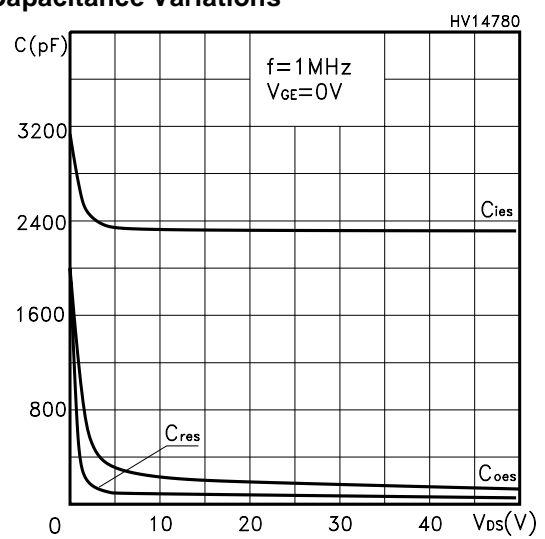
Transconductance



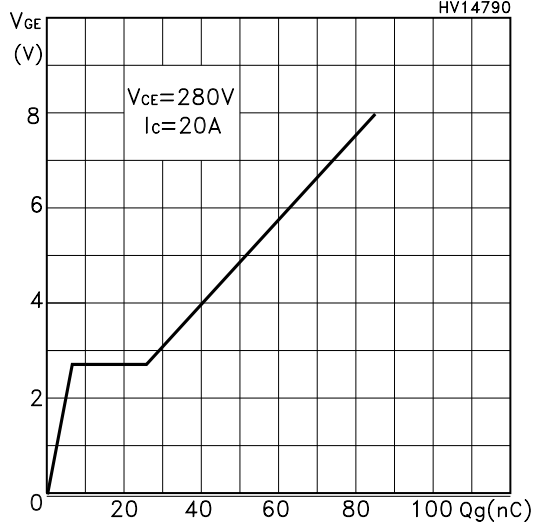
Collector-Emitter On Voltage vs Temperature



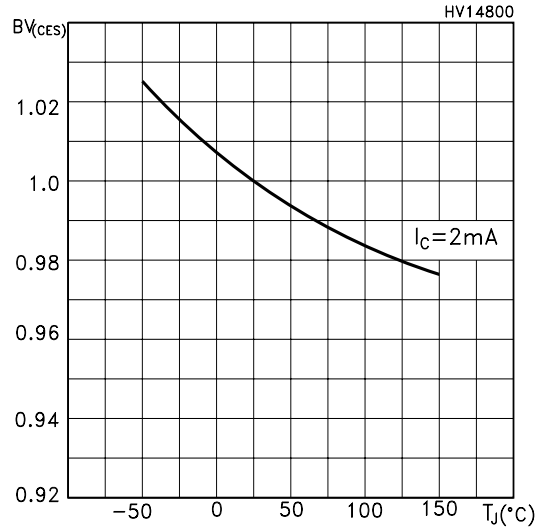
Capacitance Variations



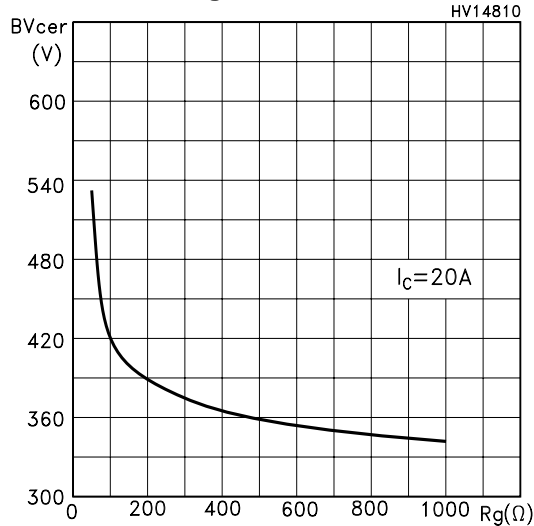
Gate Charge vs Gate-Emitter Voltage



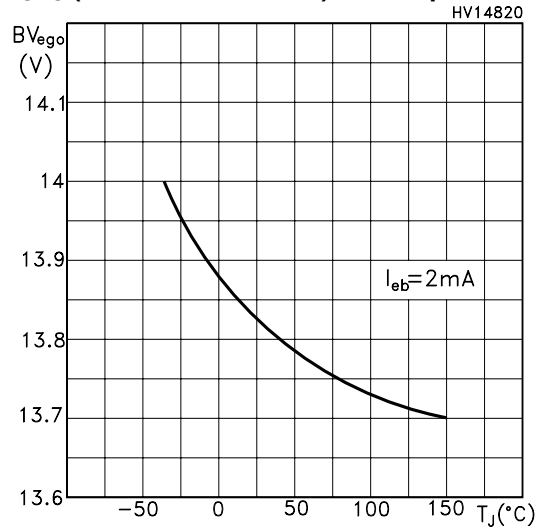
Normalized BreakDown Voltage vs Temperature



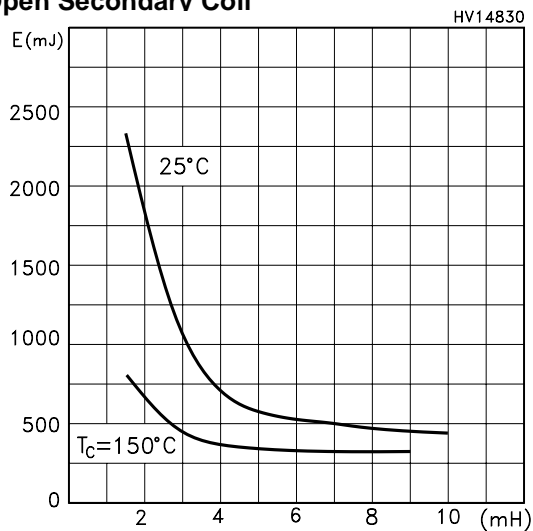
Break-Down Voltage vs Emitter Resistance



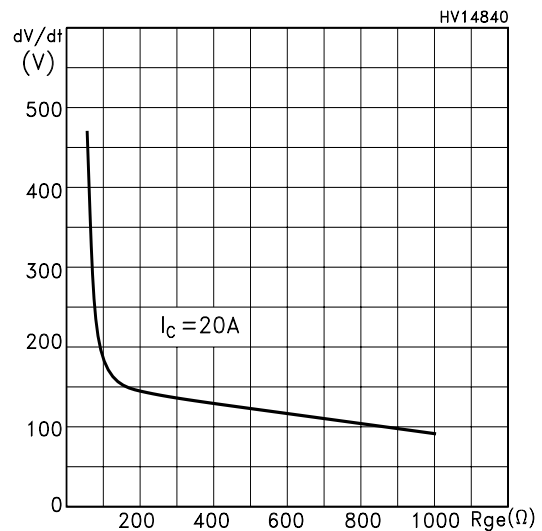
BVGE0 (Zener Gate-Emitter) vs Temperature



Self Clamped Inductive Switching Energy vs Open Secondary Coil

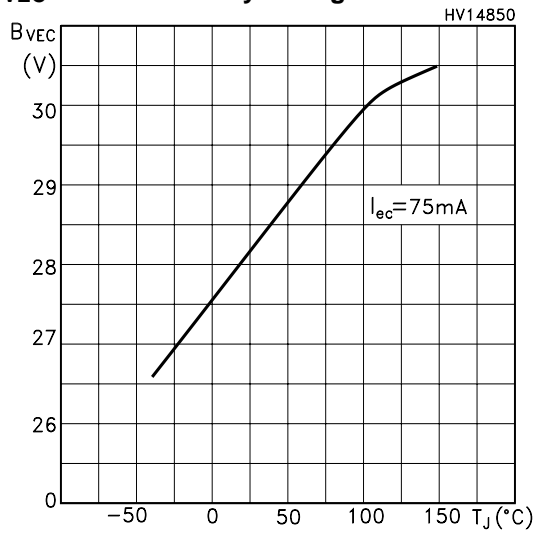


dV/dt Gate-Emitter Resistance

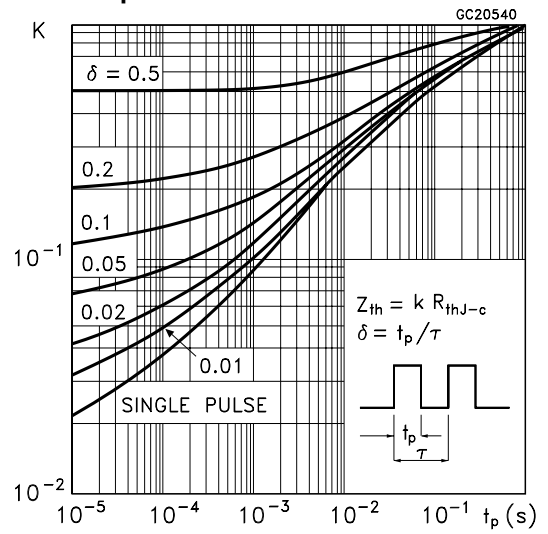


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B_{VEC} Reverse Battery Voltage



Thermal Impedance



Switching Off Safe Operating Area

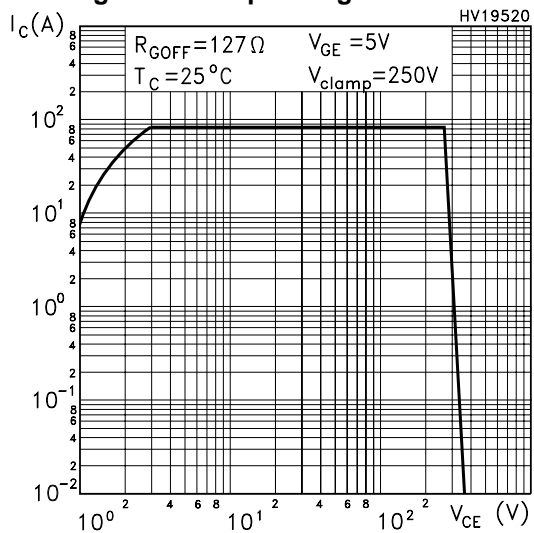


Fig. 1: Unclamped Inductive Load Test Circuit

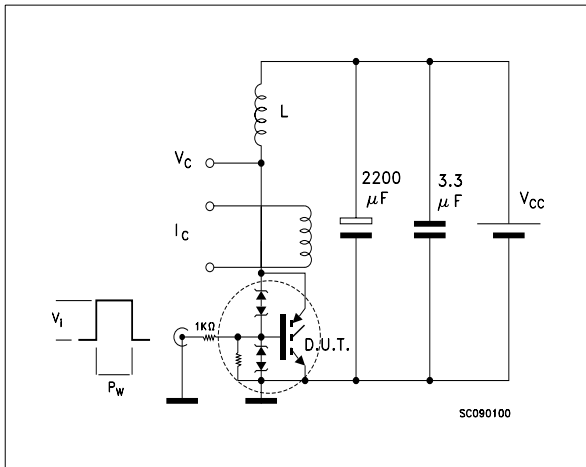


Fig. 2: Unclamped Inductive Waveform

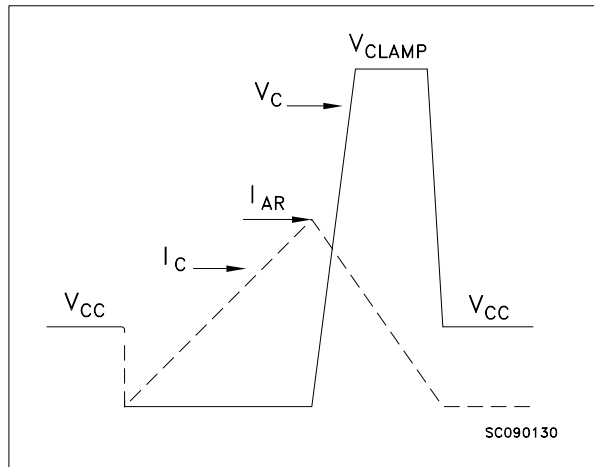


Fig. 3: Test Circuit For Inductive Load Switching And Diode Recovery Times

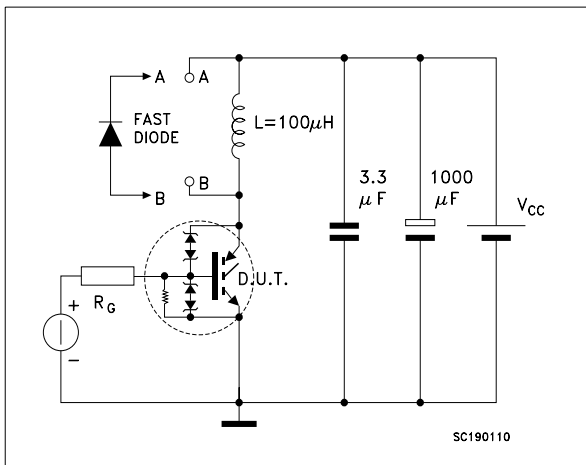
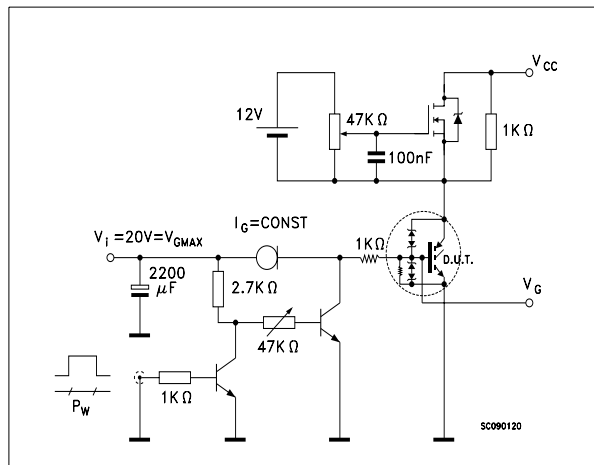
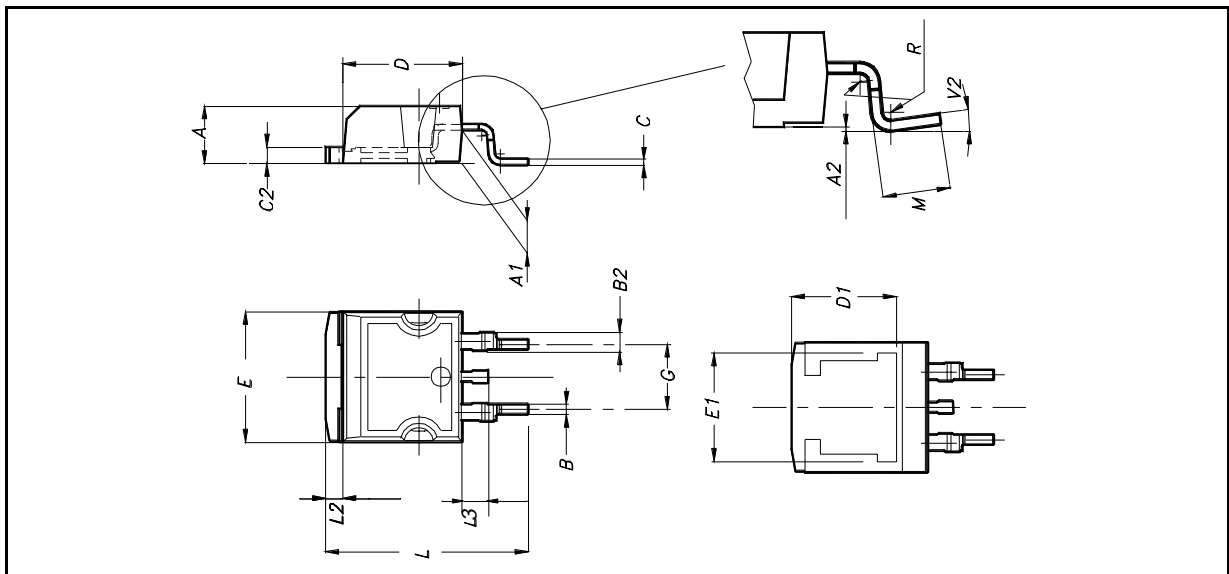


Fig. 4: Gate Charge test Circuit



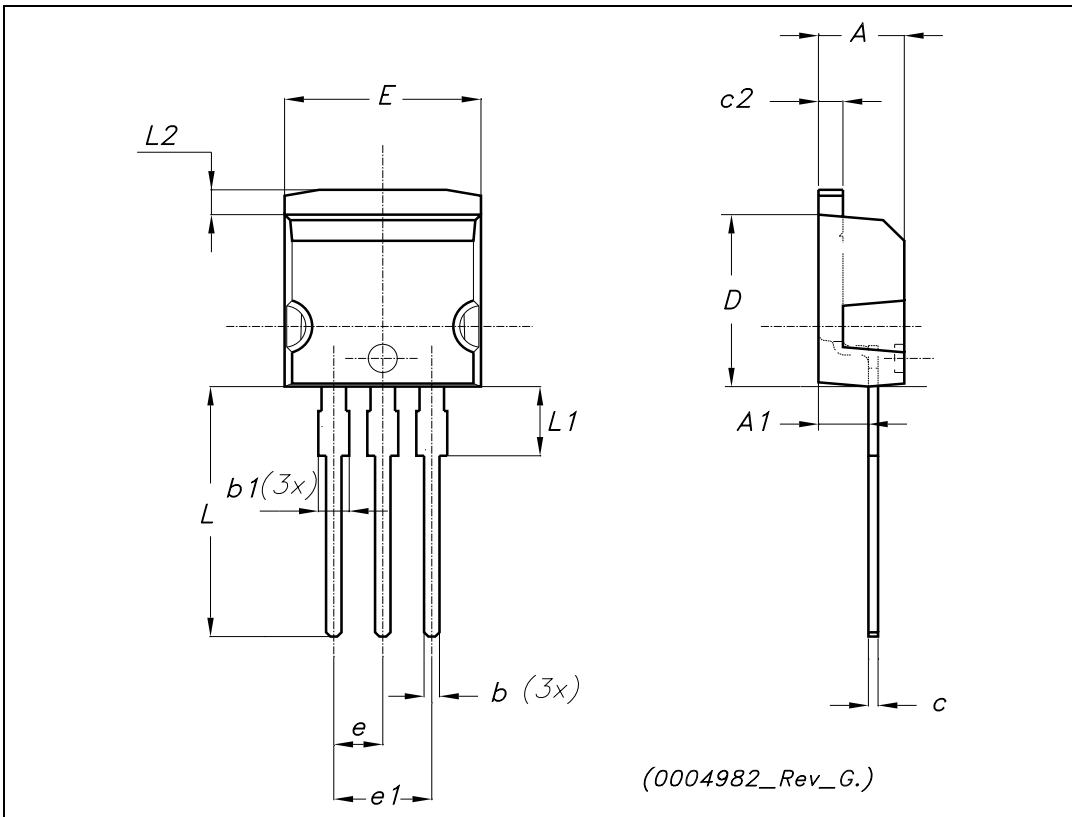
D²PAK MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0°		8°			

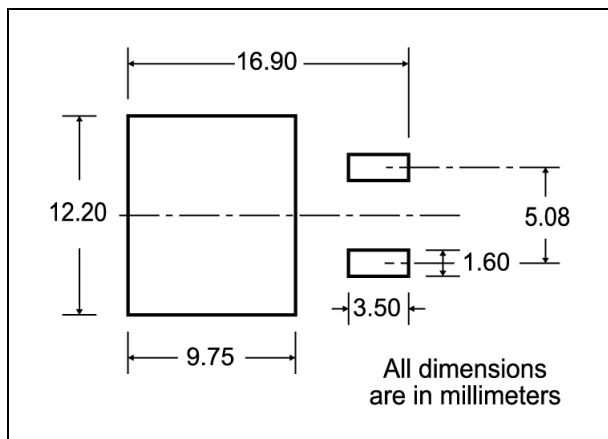


TO-262 (I²PAK) MECHANICAL DATA

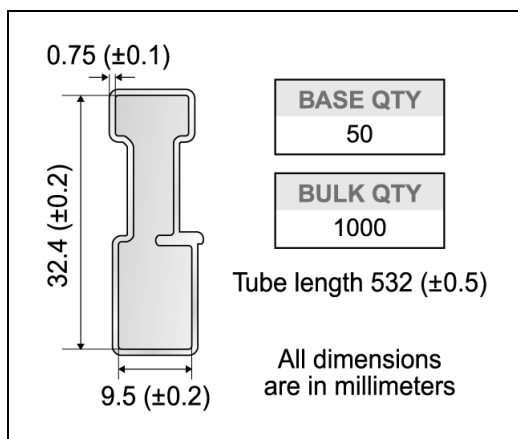
DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
A1	2.40		2.72	0.094		0.107
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.49		0.70	0.019		0.027
c2	1.23		1.32	0.048		0.052
D	8.95		9.35	0.352		0.368
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
E	10		10.40	0.393		0.410
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L2	1.27		1.40	0.050		0.055



D²PAK FOOTPRINT



TUBE SHIPMENT (no suffix)*



TAPE AND REEL SHIPMENT (suffix "T4")*

TAPE MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	10.5	10.7	0.413	0.421
B0	15.7	15.9	0.618	0.626
D	1.5	1.6	0.059	0.063
D1	1.59	1.61	0.062	0.063
E	1.65	1.85	0.065	0.073
F	11.4	11.6	0.449	0.456
K0	4.8	5.0	0.189	0.197
P0	3.9	4.1	0.153	0.161
P1	11.9	12.1	0.468	0.476
P2	1.9	2.1	0.075	0.082
R	50		1.574	
T	0.25	0.35	0.0098	0.0137
W	23.7	24.3	0.933	0.956

REEL MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	24.4	26.4	0.960	1.039
N	100		3.937	
T		30.4		1.197

BASE QTY	BULK QTY
1000	1000

TAPE AND REEL SHIPMENT (suffix "T4")*

* on sales type
10/11



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